

DERWENT-ACC-NO: 2003-413803

DERWENT-WEEK: 200339

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TITLE: Method for fabricating capacitor of semiconductor device

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PRIORITY-DATA: 2001KR-0038167 (June 29, 2001)

PATENT-FAMILY:

PUB-NO	PAGES	PUB-DATE	MAIN-IPC
KR 2003002518 A		January 9, 2003	N/A
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APPLICATION-DATA:

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KR2003002518A		N/A	
2001KR-0038167		June 29, 2001	

INT-CL (IPC): H01L027/108

ABSTRACTED-PUB-NO: KR2003002518A

BASIC-ABSTRACT:

NOVELTY - A method for fabricating a capacitor of a semiconductor device is provided to improve resolution and uniformity of critical dimension(CD) and to remove a pattern defect caused by defocus by making two masks having a line/space pattern cross each other in a storage electrode region.

DETAILED DESCRIPTION - An interlayer dielectric(11) having a contact plug(13)

is formed on a semiconductor substrate. An oxide layer for a storage electrode is formed on the interlayer dielectric. The storage electrode region is defined in the oxide layer for the storage electrode, wherein a double exposure process is performed to make the two masks having the line/space pattern overlap each other. A nitride layer is formed to planarize the resultant structure. The nitride layer is etched by using a difference of etch selectivity of the nitride layer and the oxide layer. The oxide layer is exposed and eliminated to expose the storage electrode region and the contact plug. A conductive layer for the storage electrode connected to the contact plug is formed on the resultant structure. A photoresist layer is applied on the resultant structure. The photoresist layer and the conductive layer for the storage electrode are etched to expose the nitride layer. The photoresist layer is removed to form a concave storage electrode.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD FABRICATE CAPACITOR SEMICONDUCTOR  
DEVICE

DERWENT-CLASS: L03 U13 U14

CPI-CODES: L04-C14A;

EPI-CODES: U13-C04B1A; U14-A03B4;

SECONDARY-ACC-NO:

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